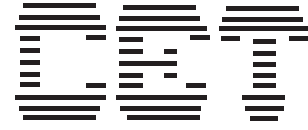


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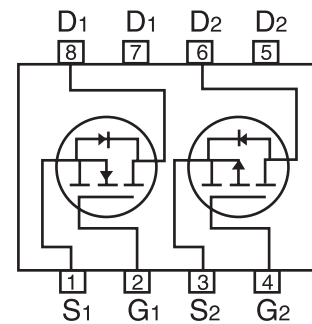
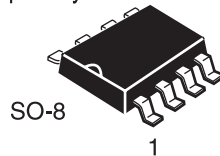
PRELIMINARY

## Dual Enhancement Mode Field Effect Transistor(N and P Channel)

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### FEATURES

- 30V , 5.8A ,  $R_{DS(ON)}=37m\ \Omega$  @  $V_{GS}=10V$ .  
 $R_{DS(ON)}=55m\ \Omega$  @  $V_{GS}=4.5V$ .  
 -30V , -4.9A ,  $R_{DS(ON)}=53m\ \Omega$  @  $V_{GS}=-10V$ .  
 $R_{DS(ON)}=95m\ \Omega$  @  $V_{GS}=-4.5V$ .
- Super high dense cell design for extremely low  $R_{DS(ON)}$ .
- High power and current handling capability.
- Surface Mount Package.



### ABSOLUTE MAXIMUM RATINGS ( $T_A=25^\circ\text{C}$ unless otherwise noted)

| Parameter   | Symbol         | N-Channel  | P-Channel | Unit             |
|---|----------------|------------|-----------|------------------|
| Drain-Source Voltage  | $V_{DS}$       | 30         | -30       | V                |
| Gate-Source Voltage   | $V_{GS}$       | $\pm 20$   | $\pm 20$  | V                |
| Drain Current-Continuous <sup>a</sup> @ $T_J=125^\circ\text{C}$<br>-Pulsed <sup>b</sup> | $I_D$          | $\pm 5.8$  | $\pm 4.9$ | A                |
|   | $I_{DM}$       | $\pm 30$   | $\pm 30$  | A                |
| Drain-Source Diode Forward Current <sup>a</sup>   | $I_S$          | 1.7        | -1.7      | A                |
| Maximum Power Dissipation <sup>a</sup>  | $P_D$          | 2          |           | W                |
| Operating Junction and Storage Temperature Range  | $T_J, T_{STG}$ | -55 to 150 |           | $^\circ\text{C}$ |

### THERMAL CHARACTERISTICS

|  |                 |      |                    |
|--|-----------------|------|--------------------|
| Thermal Resistance, Junction-to-Ambient <sup>a</sup> | $R_{\theta JA}$ | 62.5 | $^\circ\text{C/W}$ |
|--|-----------------|------|--------------------|

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## N-Channel ELECTRICAL CHARACTERISTICS (TA=25°C unless otherwise noted)

| Parameter                                    | Symbol              | Condition   | Min | Typ <sup>c</sup> | Max  | Unit |
|--|---------------------|---|-----|------------------|------|------|
| <b>OFF CHARACTERISTICS</b>                   |                     |   |     |                  |      |      |
| Drain-Source Breakdown Voltage               | BV <sub>DSS</sub>   | V <sub>GS</sub> =0V, I <sub>D</sub> =250μA  | 30  |                  |      | V    |
| Zero Gate Voltage Drain Current              | I <sub>DSS</sub>    | V <sub>DS</sub> =30V, V <sub>GS</sub> =0V   |     |                  | 1    | μA   |
| Gate-Body Leakage                            | I <sub>GSS</sub>    | V <sub>GS</sub> =±20V, V <sub>DS</sub> =0V  |     |                  | ±100 | nA   |
| <b>ON CHARACTERISTICS<sup>c</sup></b>        |                     |   |     |                  |      |      |
| Gate Threshold Voltage                       | V <sub>GS(th)</sub> | V <sub>DS</sub> =V <sub>GS</sub> , I <sub>D</sub> =250μA                                      | 1   | 1.4              | 3    | V    |
| Drain-Source On-State Resistance             | R <sub>DS(ON)</sub> | V <sub>GS</sub> =10V, I <sub>D</sub> =5.8A  |     | 30               | 37   | mΩ   |
|  |                     | V <sub>GS</sub> =4.5V, I <sub>D</sub> =4.7A   |     | 41               | 55   | mΩ   |
| On-State Drain Current                       | I <sub>D(ON)</sub>  | V <sub>GS</sub> =10V, V <sub>DS</sub> =5V   | 15  |                  |      | A    |
| Forward Transconductance                     | g <sub>FS</sub>     | V <sub>DS</sub> =15V, I <sub>D</sub> =5.8A  |     | 12               |      | S    |
| <b>DYNAMIC CHARACTERISTICS<sup>c</sup></b>   |                     |   |     |                  |      |      |
| Input Capacitance                            | C <sub>ISS</sub>    | V <sub>DS</sub> =15V, V <sub>GS</sub> =0V<br>f=1.0MHz   |     | 500              | 650  | pF   |
| Output Capacitance                           | C <sub>OSS</sub>    |   |     | 267              | 350  | pF   |
| Reverse Transfer Capacitance                 | C <sub>RSS</sub>    |   |     | 93               | 120  | pF   |
| <b>SWITCHING CHARACTERISTICS<sup>c</sup></b> |                     |   |     |                  |      |      |
| Turn-On Delay Time                           | t <sub>D(ON)</sub>  | V <sub>DD</sub> =15V,<br>I <sub>D</sub> =1A,<br>V <sub>GS</sub> =10V,<br>R <sub>GEN</sub> =6Ω |     | 9                | 15   | ns   |
| Rise Time                                    | t <sub>r</sub>      |   |     | 9                | 20   | ns   |
| Turn-Off Delay Time                          | t <sub>D(OFF)</sub> |   |     | 25               | 50   | ns   |
| Fall Time                                    | t <sub>f</sub>      |   |     | 20               | 35   | ns   |
| Total Gate Charge                            | Q <sub>g</sub>      | V <sub>DS</sub> =15V, I <sub>D</sub> =5.8A,<br>V <sub>GS</sub> =10V                           |     | 34               | 55   | nC   |
| Gate-Source Charge                           | Q <sub>gs</sub>     |   |     | 6                |      | nC   |
| Gate-Drain Charge                            | Q <sub>gd</sub>     |   |     | 7                |      | nC   |

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## P-Channel ELECTRICAL CHARACTERISTICS (TA=25 °C unless otherwise noted)

| Parameter                                    | Symbol              | Condition   | Min | Typ <sup>c</sup> | Max  | Unit |
|--|---------------------|---|-----|------------------|------|------|
| <b>OFF CHARACTERISTICS</b>                   |                     |   |     |                  |      |      |
| Drain-Source Breakdown Voltage               | BV <sub>DSS</sub>   | V <sub>GS</sub> =0V, I <sub>D</sub> =-250μA   | -30 |                  |      | V    |
| Zero Gate Voltage Drain Current              | I <sub>DSS</sub>    | V <sub>DS</sub> =-30V, V <sub>GS</sub> =0V  |     |                  | -1   | μA   |
| Gate-Body Leakage                            | I <sub>GSS</sub>    | V <sub>GS</sub> =±20V, V <sub>DS</sub> =0V  |     |                  | ±100 | nA   |
| <b>ON CHARACTERISTICS<sup>b</sup></b>        |                     |   |     |                  |      |      |
| Gate Threshold Voltage                       | V <sub>GS(th)</sub> | V <sub>DS</sub> =V <sub>GS</sub> , I <sub>D</sub> =-250μA   | -1  | -1.5             | -3   | V    |
| Drain-Source On-State Resistance             | R <sub>DS(ON)</sub> | V <sub>GS</sub> =-10V, I <sub>D</sub> =-4.9A  |     | 43               | 53   | mΩ   |
|  |                     | V <sub>GS</sub> =-4.5V, I <sub>D</sub> =-3.6A   |     | 70               | 95   | mΩ   |
| On-State Drain Current                       | I <sub>D(ON)</sub>  | V <sub>DS</sub> =-5V, V <sub>GS</sub> =-10V   | -20 |                  |      | A    |
| Forward Transconductance                     | g <sub>FS</sub>     | V <sub>DS</sub> =-15V, I <sub>D</sub> =-4.9A  | 5   | 10               |      | S    |
| <b>DYNAMIC CHARACTERISTICS<sup>c</sup></b>   |                     |   |     |                  |      |      |
| Input Capacitance                            | C <sub>ISS</sub>    | V <sub>DS</sub> =-15V, V <sub>GS</sub> =0V<br>f=1.0MHz  |     | 860              | 1120 | pF   |
| Output Capacitance                           | C <sub>OSS</sub>    |   |     | 457              | 600  | pF   |
| Reverse Transfer Capacitance                 | C <sub>RSS</sub>    |   |     | 140              | 190  | pF   |
| <b>SWITCHING CHARACTERISTICS<sup>c</sup></b> |                     |   |     |                  |      |      |
| Turn-On Delay Time                           | t <sub>D(ON)</sub>  | V <sub>D</sub> =-15V,<br>R <sub>L</sub> =15Ω<br>I <sub>D</sub> =-1A,<br>V <sub>GEN</sub> =-10V,<br>R <sub>GEN</sub> =6Ω |     | 8                | 15   | ns   |
| Rise Time                                    | t <sub>r</sub>      |   |     | 12               | 20   | ns   |
| Turn-Off Delay Time                          | t <sub>D(OFF)</sub> |   |     | 23               | 40   | ns   |
| Fall Time                                    | t <sub>f</sub>      |   |     | 14               | 25   | ns   |
| Total Gate Charge                            | Q <sub>g</sub>      | V <sub>DS</sub> =-15V, I <sub>D</sub> =-4.9A,<br>V <sub>GS</sub> =-10V  |     | 16               | 25   | nC   |
| Gate-Source Charge                           | Q <sub>gs</sub>     |   |     | 5                |      | nC   |
| Gate-Drain Charge                            | Q <sub>gd</sub>     |   |     | 2                |      | nC   |

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## ELECTRICAL CHARACTERISTICS ( $T_A=25^\circ\text{C}$ unless otherwise noted)

| Parameter   | Symbol          | Condition                                    | Min  | Typ <sup>c</sup> | Max  | Unit |
|---|-----------------|--|------|------------------|------|------|
| <b>DRAIN-SOURCE DIODE CHARACTERISTICS<sup>b</sup></b> |                 |  |      |                  |      |      |
| Diode Forward Voltage                                 | V <sub>SD</sub> | V <sub>GS</sub> = 0V, I <sub>S</sub> = 1.7A  | N-Ch | 0.7              | 1.2  | V    |
|   |                 | V <sub>GS</sub> = 0V, I <sub>S</sub> = -1.7A | P-Ch | -0.8             | -1.2 |      |

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### Notes

- a. Surface Mounted on FR4 Board,  $t \leq 10\text{sec}$ .
- b. Pulse Test: Pulse Width  $\leq 300\ \mu\text{s}$ , Duty Cycle  $\leq 2\%$ .
- c. Guaranteed by design, not subject to production testing.

N-Channel

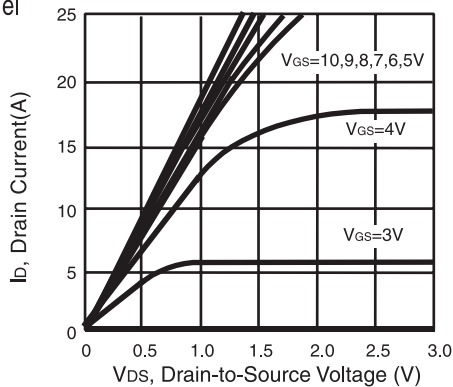


Figure 1. Output Characteristics

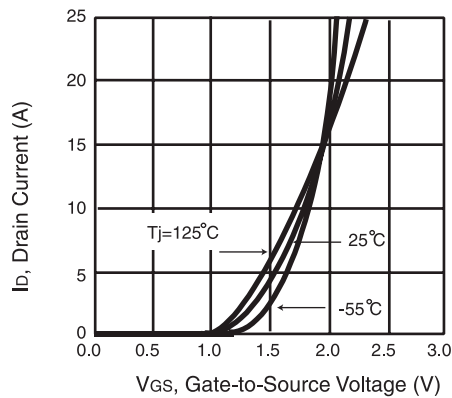


Figure 2. Transfer Characteristics

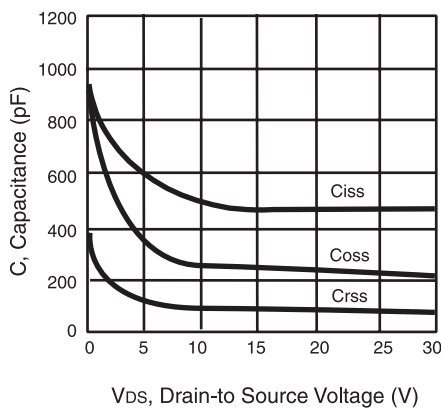


Figure 3. Capacitance

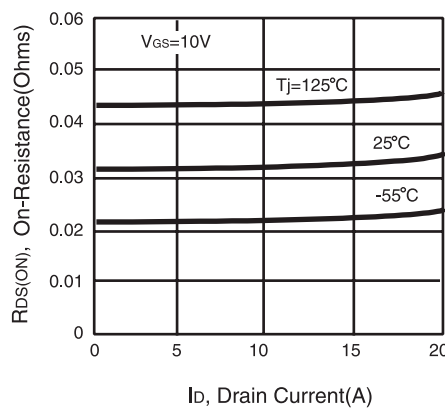
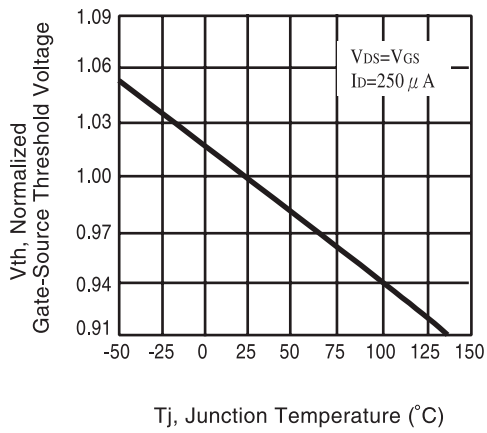


Figure 4. On-Resistance Variation with Drain Current and Temperature

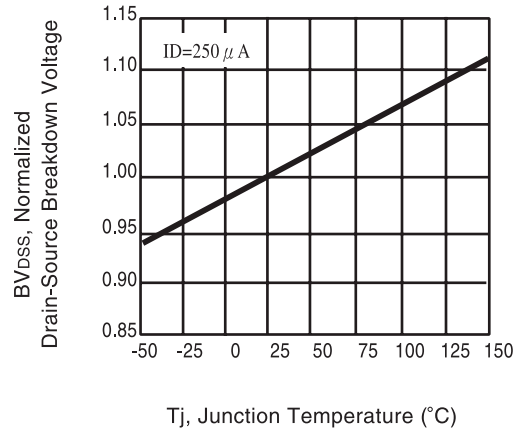
# CEM4539

## N-Channel

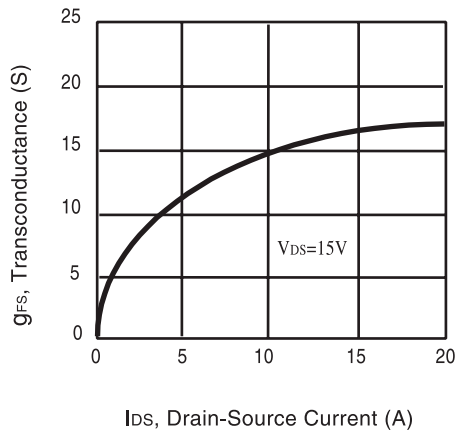
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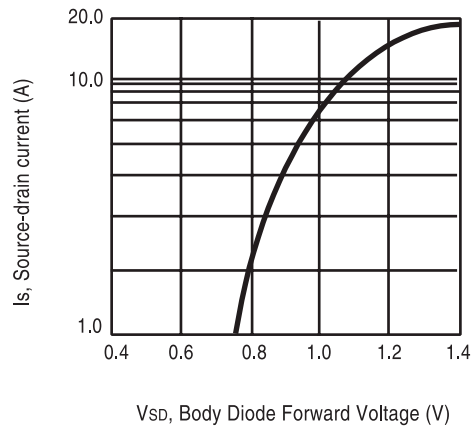
**Figure 5. Gate Threshold Variation with Temperature**



**Figure 6. Breakdown Voltage Variation with Temperature**



**Figure 7. Transconductance Variation with Drain Current**



**Figure 8. Body Diode Forward Voltage Variation with Source Current**

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## P-Channel

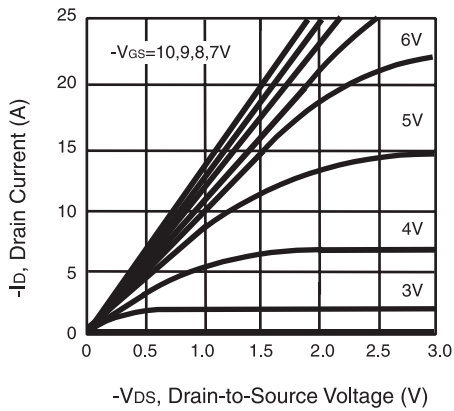


Figure 1. Output Characteristics

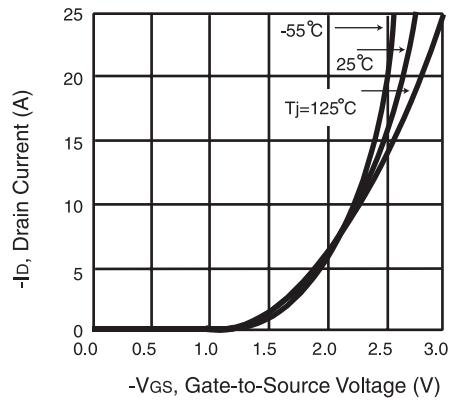


Figure 2. Transfer Characteristics

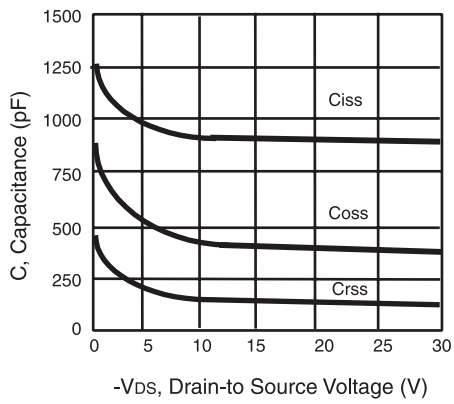


Figure 3. Capacitance

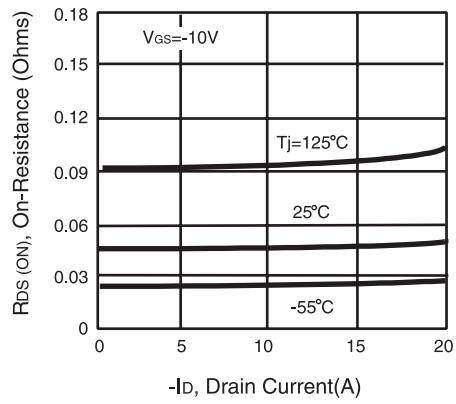


Figure 4. On-Resistance Variation with Drain Current and Temperature

# CEM4539

## P-Channel

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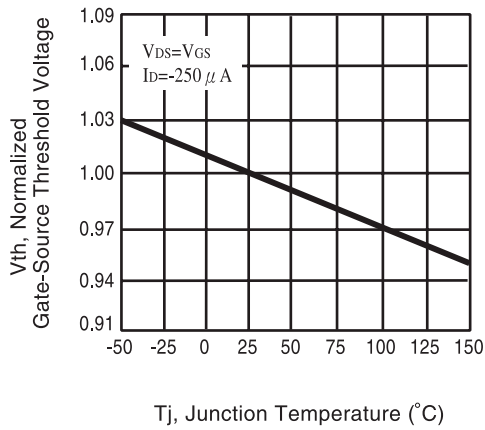


Figure 5. Gate Threshold Variation with Temperature

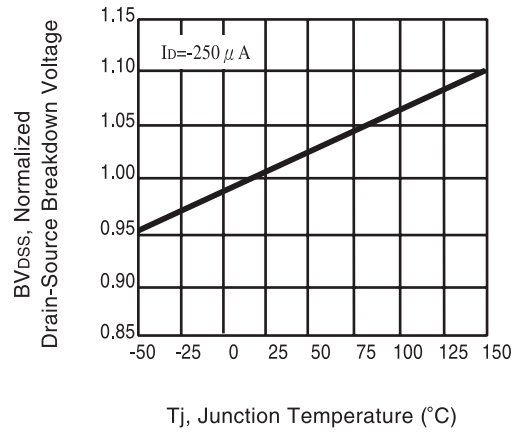


Figure 6. Breakdown Voltage Variation with Temperature

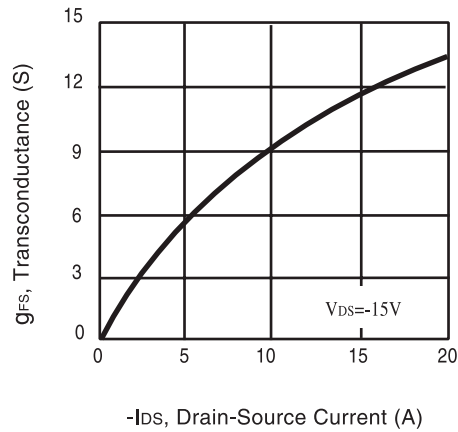


Figure 7. Transconductance Variation with Drain Current

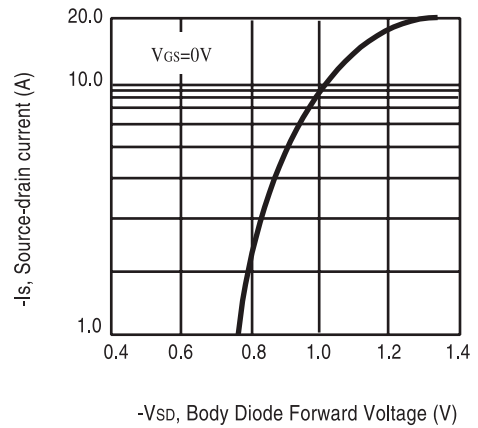
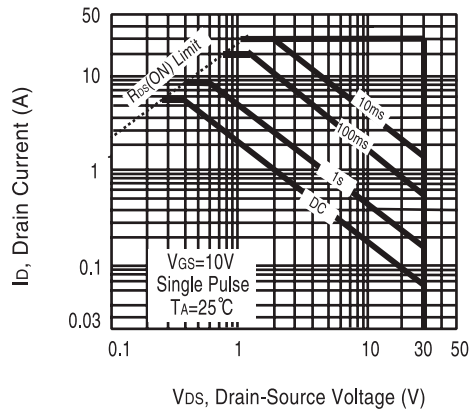
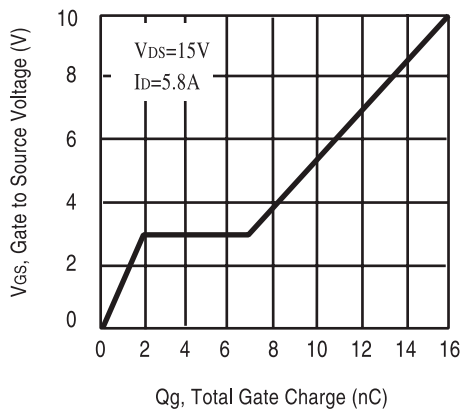


Figure 8. Body Diode Forward Voltage Variation with Source Current

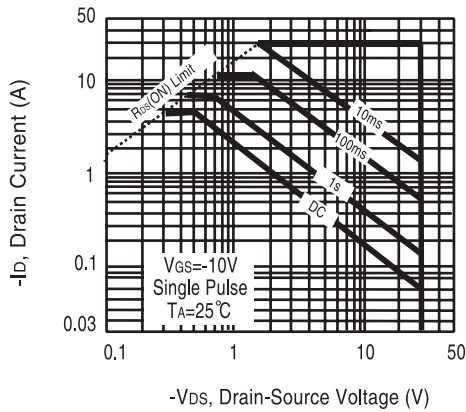
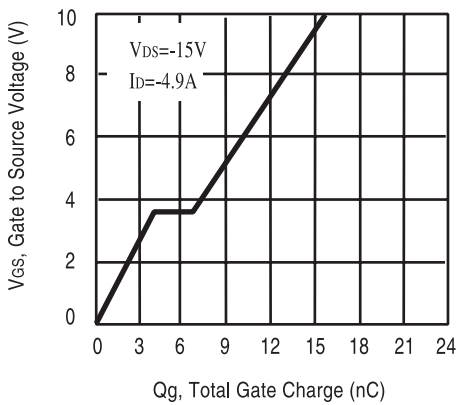
# CEM4539

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## N-Channel



## P-Channel





# CEM4539

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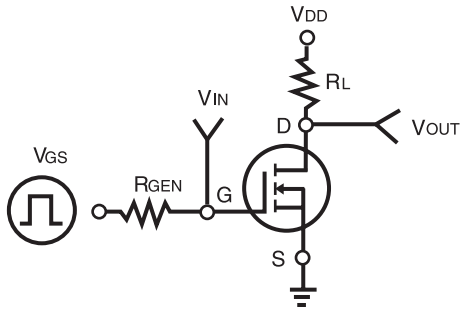


Figure 11. Switching Test Circuit

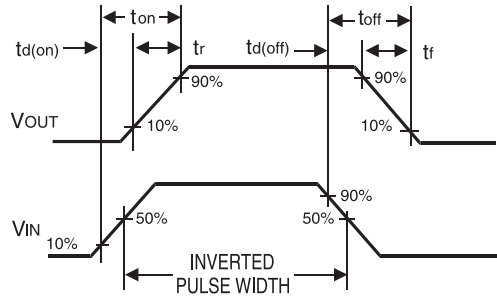


Figure 12. Switching Waveforms

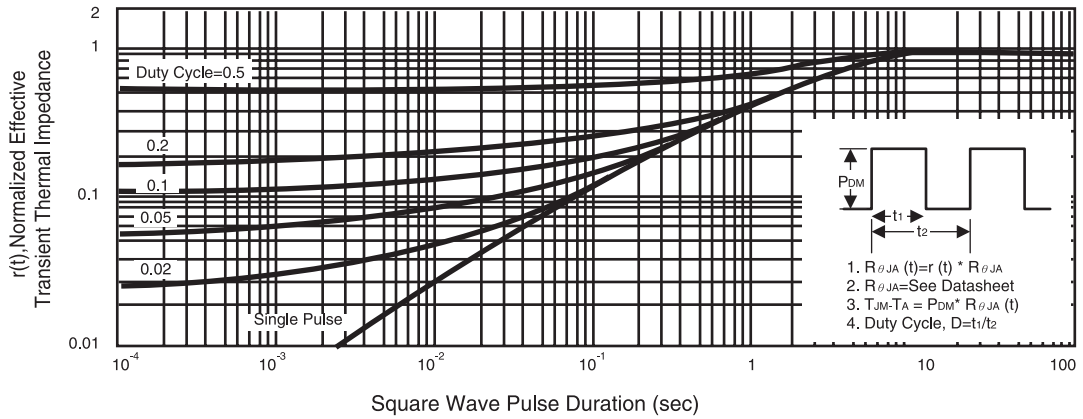


Figure 13. Normalized Thermal Transient Impedance Curve